

UTC UNISONIC TECHNOLOGIES CO., LTD

13005BA

Preliminary

NPN SILICON TRANSISTOR

NPN SILICON POWER TRANSISTORS

DESCRIPTION

These devices are designed for high-voltage, high-speed power switching inductive circuits where fall time is critical. They are particularly suited for 115 and 220 V SWITCHMODE.

FEATURES

- * V_{CEO(SUS)}= 800 V
- * Reverse bias SOA with inductive loads @ T_C = 100°C
- * Inductive switching matrix 2 to 4 Amp, 25 and 100°C
- t_c @ 3A, 100°C is 180 ns (Typ)
- * 800V blocking capability
- * SOA and switching applications information

APPLICATIONS

- * Switching regulator's, inverters
- * Motor controls
- * Solenoid/Relay drivers
- * Deflection circuits

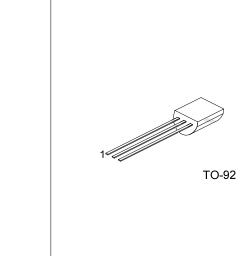
ORDERING INFORMATION

| Ordering Number | | Deekege | Pin Assignment | | | Deaking | |
|-----------------|----------------|---------|----------------|---|---|-----------|--|
| Lead Free | Halogen Free | Package | 1 | 2 | 3 | Packing | |
| 13005BAL-T92-B | 13005BAG-T92-B | TO-92 | В | С | Е | Tape Box | |
| 13005BAL-T92-K | 13005BAG-T92-K | TO-92 | В | С | Е | Bulk | |
| 13005BAL-T92-R | 13005BAG-T92-R | TO-92 | В | С | Е | Tape Reel | |

| 13005BA <u>Ļ-Т92</u> - <u></u> | | |
|--------------------------------|-----------------|------------------------------------|
| | (1)Packing Type | (1) B: Bluk, K: Bulk, R: Tape Reel |
| | (2)Package Type | (2) T92: TO-92 |
| | (3)Lead Free | (3) L: Lead Free, G: Halogen Free |
| | | |

MARKING INFORMATION

| PACKAGE | MARKING |
|---------|--|
| TO-92 | UTC 13005BA L: Lead Free G: Halogen Free Data Code 1 2 3 |



Preliminary

NPN SILICON TRANSISTOR

■ ABSOLUTE MAXIMUM RATINGS

| PARAMETER | | SYMBOL | RATINGS | UNIT | |
|--|------------|-----------------------|------------|------|--|
| Collector-Emitter Voltage | | V _{CEO(SUS)} | 400 | V | |
| Collector-Emitter Voltage (V _{BE} =0) | | V _{CES} | 800 | V | |
| Collector-Base Voltage | | V _{CBO} | 800 | V | |
| Emitter Base Voltage | | V _{EBO} | 9 | V | |
| Collector Current | Continuous | Ι _C | 3 | А | |
| | Peak (1) | I _{CM} | 8 | А | |
| | Continuous | Ι _Β | 2 | А | |
| Base Current | Peak (1) | I _{BM} | 4 | А | |
| | Continuous | Ι _Ε | 6 | А | |
| Emitter Current | Peak (1) | I _{EM} | 12 | А | |
| Power Dissipation at T _A =25°C | | PD | 1 | W | |
| Junction Temperature | | TJ | -65 ~ +150 | °C | |
| Storage Temperature Range | | T _{STG} | -65 ~ +150 | °C | |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---------------------|-----------------|---------|------|
| Junction to Ambient | θ_{JA} | 150 | °C/W |
| Junction to Case | θ _{JC} | 112 | °C/W |

■ ELECTRICAL CHARACTERISTICS (T_c=25°C, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------------------------|-----------------------|--|-----|-------|-----|------|
| OFF CHARACTERISTICS (Note 1) | | | | | | |
| Collector-Emitter Sustaining Voltage | V _{CEO(SUS)} | I _C =10mA , I _B =0 | 800 | | | V |
| | I _{CBO} | V _{CBO} =Rated Value, V _{BE(OFF)} =1.5V | | | 1 | |
| Collector Cutoff Current | | V _{CBO} =Rated Value, | | | 5 | mA |
| | | V _{BE(OFF)} =1.5V, T _C =100°C | | | 5 | |
| Emitter Cutoff Current | I _{EBO} | V _{EB} =9V, I _C =0 | | | 1 | mA |
| ON CHARACTERISTICS (Note 1) | | | - | | | - |
| | h _{FE1} | I _C =0.5A, V _{CE} =5V | 15 | | 50 | |
| DC Current Gain | h _{FE2} | I _C =1A, V _{CE} =5V | 10 | | 60 | |
| | h _{FE3} | I _C =2A, V _{CE} =5V | 8 | | 40 | |
| | | I _C =1A, I _B =0.2A | | | 0.5 | V |
| Collector-Emitter Saturation Voltage | $V_{CE(SAT)}$ | I _C =2A, I _B =0.5A | | | 0.6 | V |
| | | I _C =4A, I _B =1A | | | 1 | V |
| | | I _C =2A, I _B =0.5A, T _A =100°C | | | 1 | V |
| | V _{BE(SAT)} | I _C =1A, I _B =0.2A | | | 1.2 | V |
| Base-Emitter Saturation Voltage | | I _C =2A, I _B =0.5A | | | 1.6 | V |
| | | I _C =2A, I _B =0.5A, T _C =100°C | | | 1.5 | V |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Current-Gain-Bandwidth Product | f⊤ | I _C =500mA, V _{CE} =10V, f=1MHz | 4 | | | MHz |
| Output Capacitance | C _{OB} | V _{CB} =10V, I _E =0, f=0.1MHz | | 65 | | pF |
| SWITCHING CHARACTERISTICS | | | | | | |
| Resistive Load (Table 1) | | | | | | |
| Delay Time | t _D | | | 0.025 | 0.1 | μs |
| Rise Time | t _R | V _{CC} =125V, I _C =2A, I _{B1} =I _{B2} =0.4A, | | 0.3 | 0.7 | μs |
| Storage Time | ts | t _P =25µs, Duty Cycle≤1% | | 1.7 | 4 | μs |
| Fall Time | t _F | | | 0.4 | 0.9 | μs |

Note: 1. Pulse Test: Pulse Width=5ms, Duty Cycle≤10%

2. Pulse Test: P_w=300µs, Duty Cycle≤2%



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